Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V			1	
		V_{DS}=30V,V_{GS}=0V, Tj=150			100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ± 20V, V_{DS}=0V			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=				

Typical Performance Characteristics

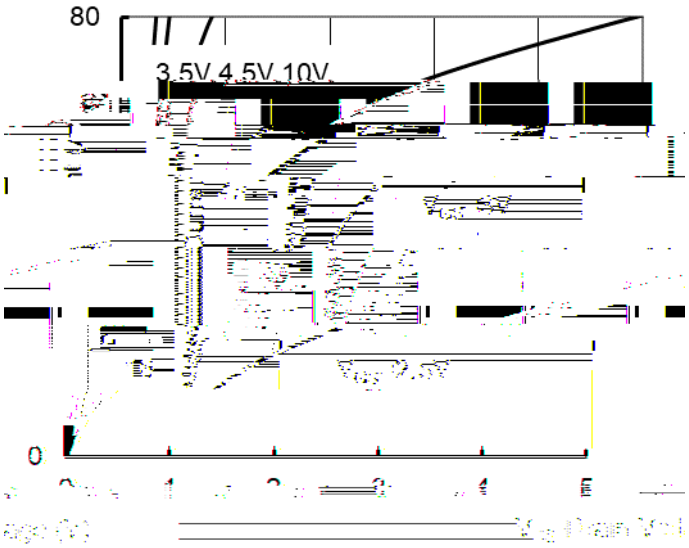


Figure 1. Output Characteristics

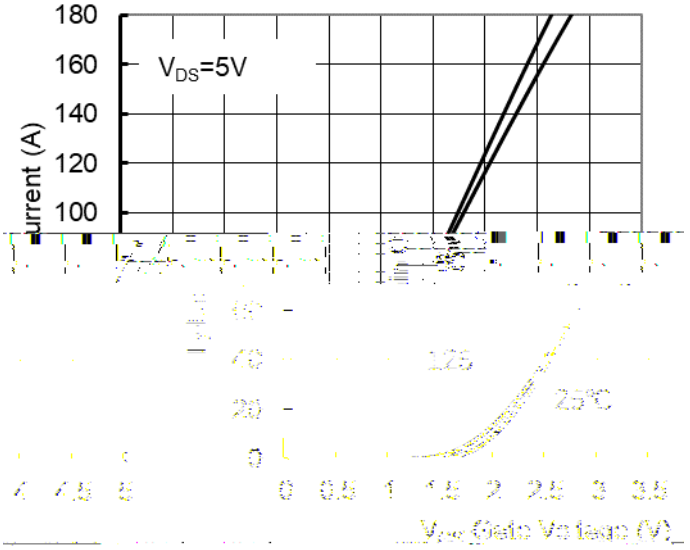


Figure 2. Transfer Characteristics

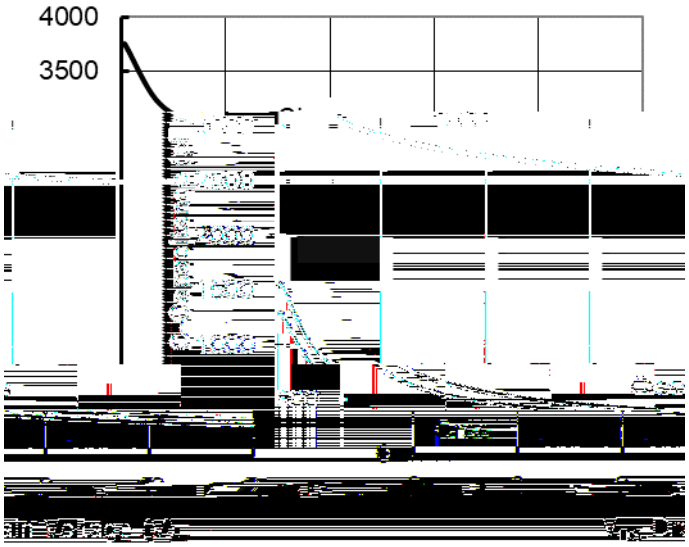


Figure 3. Capacitance Characteristics

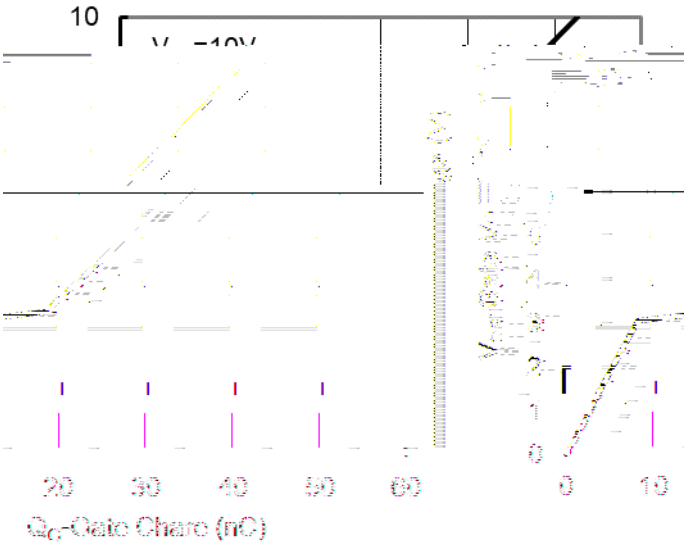
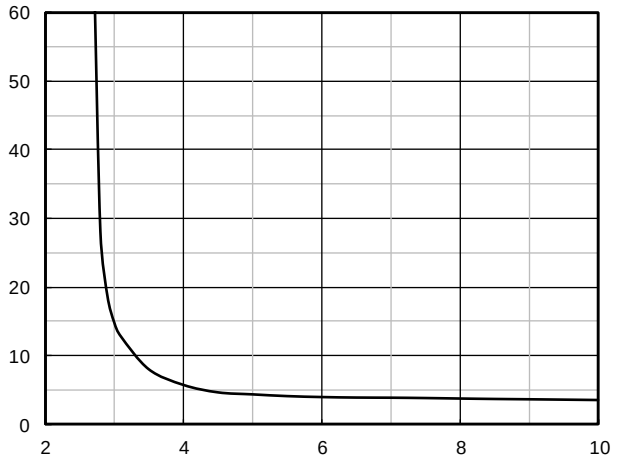


Figure 4. Gate Charge



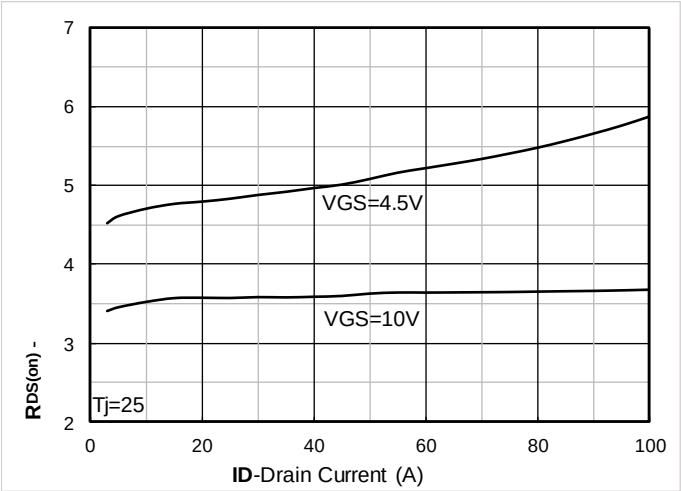


Figure 7. $R_{DS(on)}$ VS Drain Current

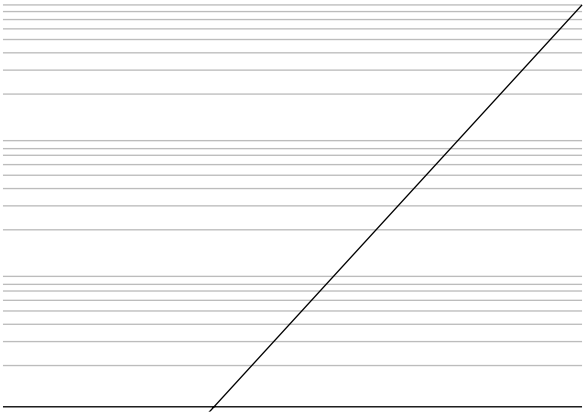


Figure 8. Forward characteristics of reverse diode

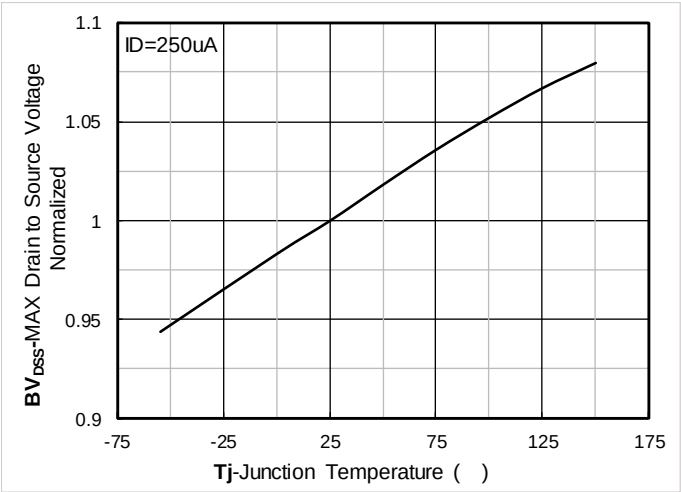


Figure 9. Normalized breakdown voltage

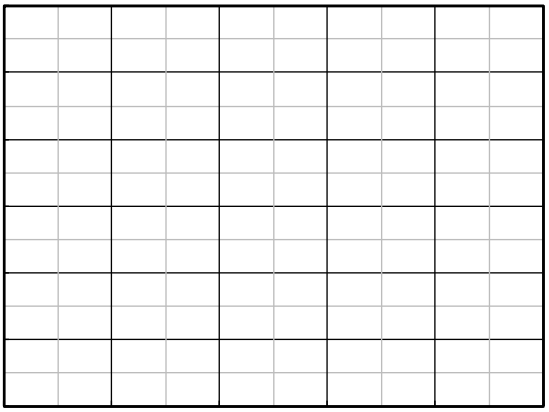


Figure 10. Normalized Threshold voltage

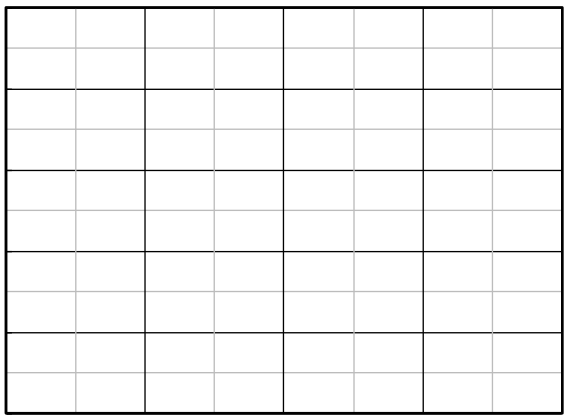
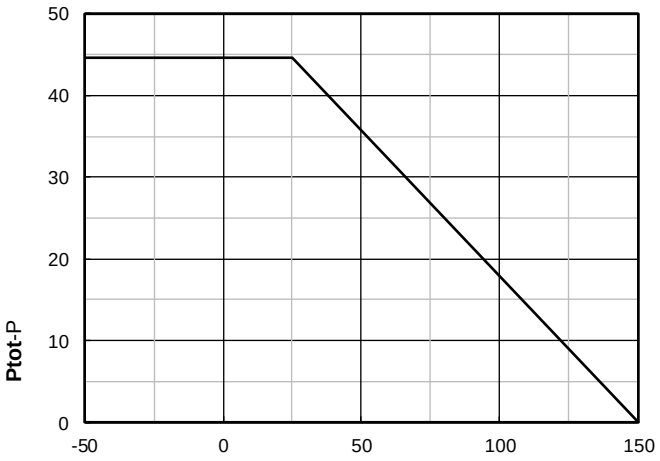


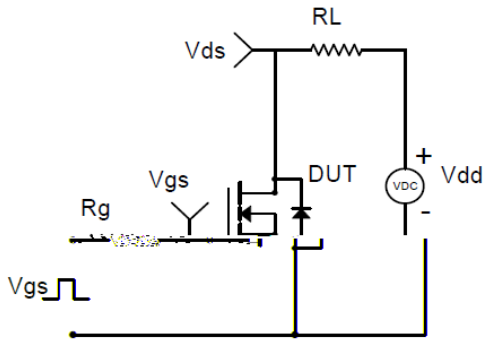
Figure 11. Current dissipation

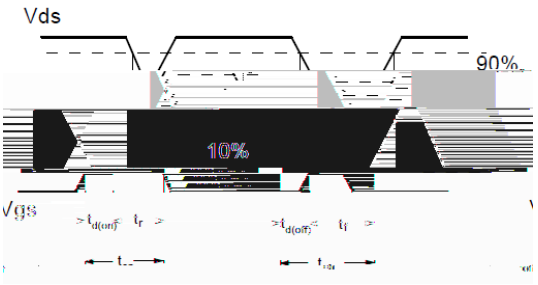


Figure

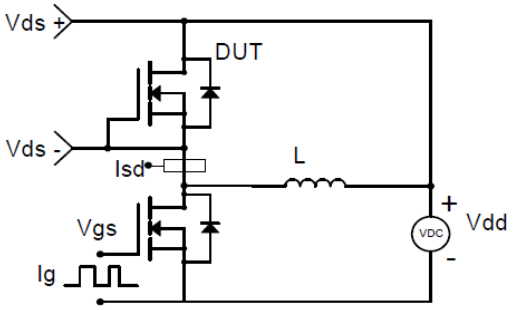
Figure 13. Normalized Maximum Transient Thermal Impedance

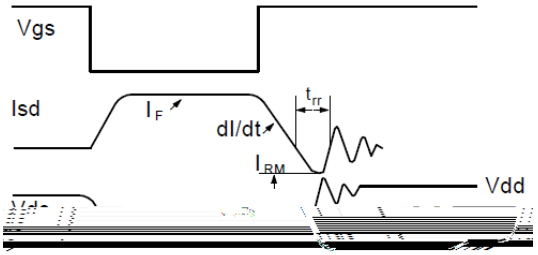
Figure 14. Safe Operation Area





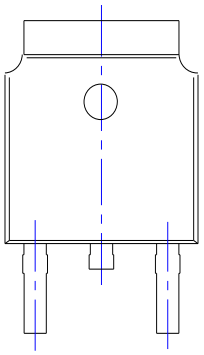
Resistive Switching Test Circuit & Waveforms

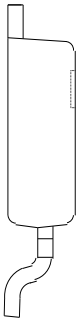


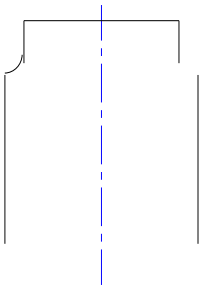


Diode Recovery Test Circuit

TO-252-B Package information







DIMENSIONS					
SYMBOL	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.087	0.091			
A3	0.035	0.039			
b	0.026	0.030			
c	0.018	0.020			
D	0.256	0.260			
D1					
D2	0.181	0.189			
E	0.390	0.398			
E1	0.236	0.240			

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.